

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a semiconductor region 103, in which an impurity of one conductivity type is doped; a gate insulation layer 105, formed on the semiconductor region 103; a gate electrode 106, formed on the gate insulation layer 105; a lightly doped layer 109a, formed in a region from the principal surface of the semiconductor region 103 to a first depth, in which a first impurity of the other conductivity type is implanted into the semiconductor region 103 with a first dose amount; and a heavily doped layer 109b, formed in a region from the principal surface of the semiconductor region 103 to a second depth, which is shallower than the first depth, in which a second impurity of the other conductivity type is implanted into the semiconductor region 103 with a second dose amount in a range of the first dose amount or more to $1 \times 10^{15}/\text{cm}^2$ or less.